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# PEMB1; PUMB1

### PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

Rev. 3 — 28 November 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package				NPN/NPN	Package
	NXP	JEITA	complement	complement	configuration	
PEMB1	SOT666	-	PEMD2	PEMH1	ultra small and flat lead	
PUMB1	SOT363	SC-88	PUMD2	PUMH1	very small	

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		8.0	1	1.2	



### 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Granhia aymbal
PIN	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		0 5 4
2	input (base) TR1	[6] [5] [4]	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa212

### 3. Ordering information

Table 4. Ordering information

Type number	Package	Package			
	Name	Description	Version		
PEMB1	-	plastic surface-mounted package; 6 leads	SOT666		
PUMB1	SC-88	plastic surface-mounted package; 6 leads	SOT363		

### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMB1	Z4
PUMB1	B*3

[1] \* = placeholder for manufacturing site code

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# 5. Limiting values

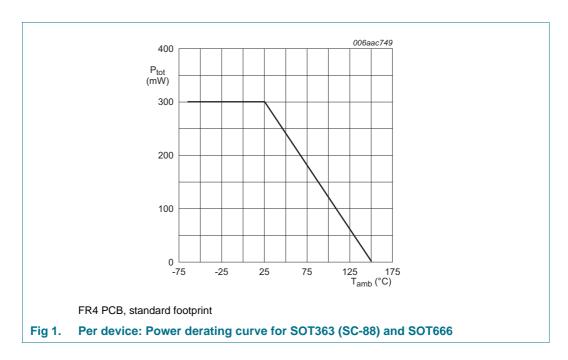
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-40	V
lo	output current		-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMB1 (SOT666)		[1][2] _	200	mW
	PUMB1 (SOT363)		<u>[1]</u> -	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMB1 (SOT666)		[1][2] _	300	mW
	PUMB1 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



### 6. Thermal characteristics

Table 7. Thermal characteristics

Parameter	Conditions	nditions Min		Тур	Max	Unit
or						
thermal resistance from junction to ambient	in free air					
PEMB1 (SOT666)		[1][2]	-	-	625	K/W
PUMB1 (SOT363)		<u>[1]</u>	-	-	625	K/W
thermal resistance from junction to ambient	in free air					
PEMB1 (SOT666)		[1][2]	-	-	417	K/W
PUMB1 (SOT363)		<u>[1]</u>	-	-	417	K/W
	thermal resistance from junction to ambient PEMB1 (SOT666) PUMB1 (SOT363) thermal resistance from junction to ambient PEMB1 (SOT666)	thermal resistance from in free air junction to ambient  PEMB1 (SOT666)  PUMB1 (SOT363)  thermal resistance from in free air junction to ambient  PEMB1 (SOT666)	thermal resistance from in free air junction to ambient  PEMB1 (SOT666) [1][2]  PUMB1 (SOT363) [1]  thermal resistance from in free air junction to ambient  PEMB1 (SOT666) [1][2]	thermal resistance from in free air junction to ambient  PEMB1 (SOT666) [1][2] -  PUMB1 (SOT363) [1] -  thermal resistance from in free air junction to ambient  PEMB1 (SOT666) [1][2] -	thermal resistance from in free air junction to ambient  PEMB1 (SOT666) [1][2]  PUMB1 (SOT363) [1]  thermal resistance from junction to ambient  PEMB1 (SOT666) [1][2]	thermal resistance from in free air junction to ambient  PEMB1 (SOT666) [1][2] 625  PUMB1 (SOT363) [1] 625  thermal resistance from junction to ambient  PEMB1 (SOT666) [1][2] 417

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

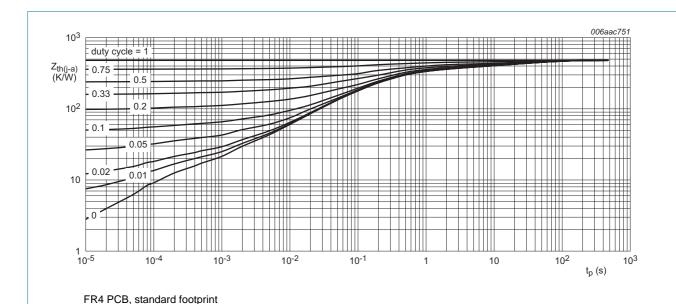


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB1 (SOT666); typical values

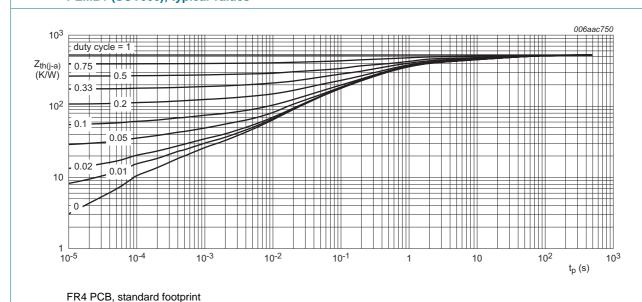


Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB1 (SOT363); typical values

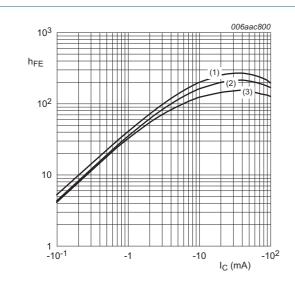
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-100	nA
	current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	<b>-5</b>	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-180	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	60	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-1.1	-0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$	-2.5	-1.7	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	$k\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; $ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor



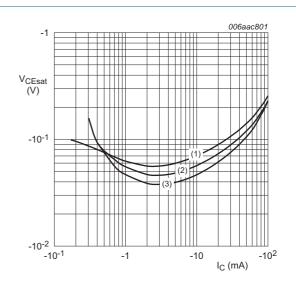
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 4. DC current gain as a function of collector current; typical values



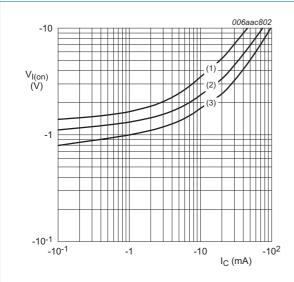
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values

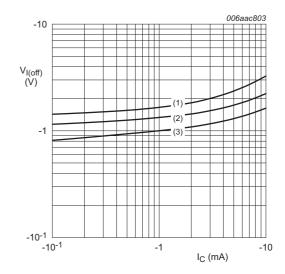


$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 6. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

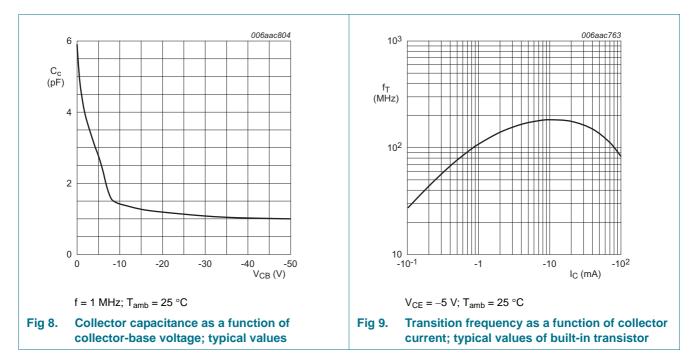
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 7. Off-state input voltage as a function of collector current; typical values

PEMB1\_PUMB1

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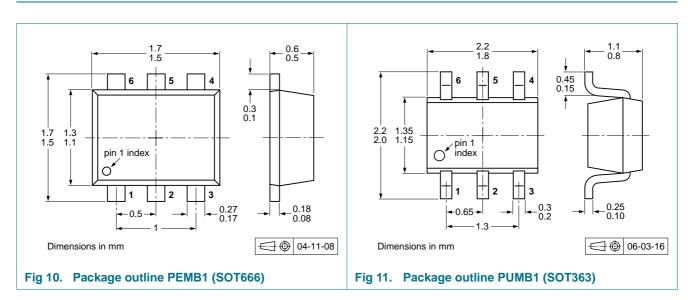


### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



PEMB1 PUMB1

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### 10. Packing information

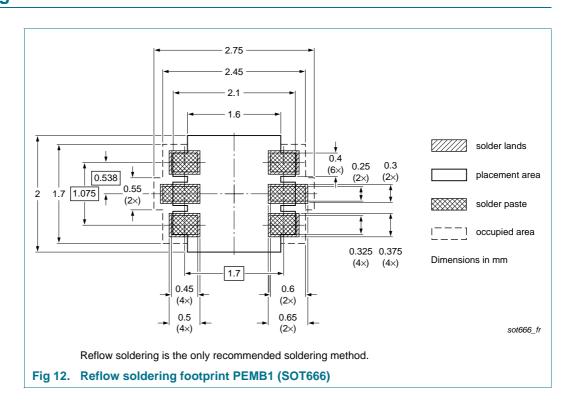
Table 9. Packing methods

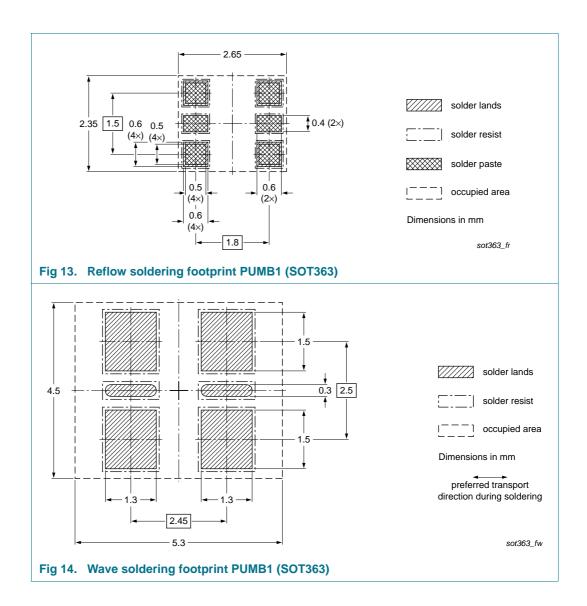
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type Pa	Package	Description		Packing quantity				
				4000	8000	10000		
PEMB1 SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-			
		4 mm pitch, 8 mm tape and reel	-	-115	-	-		
PUMB1 SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135			
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165		

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

### 11. Soldering





### 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB1_PUMB1 v.3	20111128	Product data sheet	-	PEMB1_PUMB1 v.2
Modifications:	<ul> <li>The format of guidelines of Legal texts head Section 1 "P"</li> <li>Section 4 "M"</li> <li>Figure 1 to 9</li> <li>Section 5 "Li</li> <li>Section 6 "Ti</li> <li>Table 8 "Chan Vi(off) off-state</li> <li>Section 8 "To Section 9 "Posection 10 "In Section 10 "In Section 10 "In Section 11 "Section 11 "</li></ul>	of this document has been in NXP Semiconductors. have been adapted to the noroduct profile": updated larking": updated larking": updated larking values": updated larking values val	ew company name whe dated at to $V_{I(on)}$ on-state inputed, $f_T$ added at by minimized packaged	th the new identity re appropriate. t voltage, V <sub>i(off)</sub> redefined to
PEMB1_PUMB1 v.2	20031015	Product data sheet	-	PEMB1 v.1
PEMB1 v.1	20010913	Product specification	-	-

11 of 14

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMB1\_PUMB1

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PEMB1; PUMB1

PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

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### 15. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values
6	Thermal characteristics 4
7	Characteristics 6
8	Test information 8
8.1	Quality information 8
9	Package outline 8
10	Packing information 9
11	Soldering 9
12	Revision history 11
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks13
14	Contact information
15	Contents 14

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